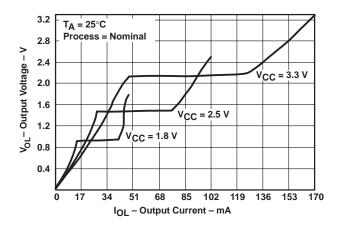
- **Member of the Texas Instruments** Widebus™ Family
- **EPIC™** (Enhanced-Performance Implanted **CMOS) Submicron Process**
- **DOC**<sup>™</sup> (Dynamic Output Control) Circuit **Dynamically Changes Output Impedance, Resulting in Noise Reduction Without Speed Degradation**
- **Dynamic Drive Capability Is Equivalent to** Standard Outputs With IOH and IOL of  $\pm$ 24 mA at 2.5-V V<sub>CC</sub>
- Overvoltage-Tolerant Inputs/Outputs Allow **Mixed-Voltage-Mode Data Communications**

- I<sub>off</sub> Supports Partial-Power-Down Mode Operation
- Ideal for Use in PC133 Registered DIMM **Applications**
- **ESD Protection Exceeds JESD 22** 
  - 2000-V Human-Body Model (A114-A)
  - 200-V Machine Model (A115-A)
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- **Package Options Include Plastic Thin** Shrink Small-Outline (DGG) and Thin Very Small-Outline (DGV) Packages

### description

A Dynamic Output Control (DOC) circuit is implemented, which, during the transition, initially lowers the output impedance to effectively drive the load and, subsequently, raises the impedance to reduce noise. Figure 1 shows typical  $V_{OI}$  vs  $I_{OI}$  and  $V_{OH}$  vs  $I_{OH}$  curves to illustrate the output impedance and drive capability of the circuit. At the beginning of the signal transition, the DOC circuit provides a maximum dynamic drive that is equivalent to a high-drive standard-output device. For more information, refer to the TI application reports, AVC Logic Family Technology and Applications, literature number SCEA006, and Dynamic Output Control (DOC™) Circuitry Technology and Applications, literature number SCEA009.



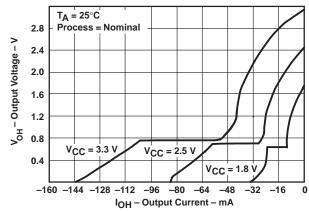


Figure 1. Output Voltage vs Output Current

This 18-bit universal bus driver is operational at 1.2-V to 3.6-V V<sub>CC</sub>, but is designed specifically for 1.65-V to 3.6-V V<sub>CC</sub> operation.

Data flow from A to Y is controlled by the output-enable  $(\overline{OE})$  input. The device operates in the transparent mode when the latch-enable ( $\overline{LE}$ ) input is low. The A data is latched if the clock (CLK) input is held at a high or low logic level. If  $\overline{\text{LE}}$  is high, the A data is stored in the latch/flip-flop on the low-to-high transition of CLK. When  $\overline{\text{OE}}$ is high, the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down,  $\overline{\sf OE}$  should be tied to  ${\sf V}_{\sf CC}$  through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.



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SCES183F - DECEMBER 1998 - REVISED FEBRUARY 2000

### description (continued)

This device is fully specified for partial-power-down applications using  $I_{off}$ . The  $I_{off}$  circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

The SN74AVC16834 is characterized for operation from -40°C to 85°C.

### terminal assignments

#### **DGG OR DGV PACKAGE** (TOP VIEW) 56 | GND NC [ NC 2 55 NC Y1 🛮 3 54 🛮 A1 GND 4 53 GND Y2 🛮 5 52 A2 Y3 **∏** 6 51 A3 50 V<sub>CC</sub> V<sub>CC</sub> 🛮 7 Y4 🛮 8 49 🛮 A4 Y5 🛮 9 48 🛮 A5 47 A6 Y6 10 GND [] 11 46 GND Y7 🛮 12 45 A7 44 🛮 A8 Y8 🛮 13 Y9 🛮 14 43 A9 Y10 ∏ 15 42 **∏** A10 Y11 🛮 16 41 🛮 A11 Y12 🛮 17 40 A12 GND **1**8 39 | GND 38 A13 Y13 19 Y14 20 37 🛮 A14 Y15 21 36 A15 V<sub>CC</sub> [] 22 35 V<sub>CC</sub> Y16 23 34 🛮 A16 Y17 **1**24 33 **A**17 GND 25 32 GND Y18 26 31 A18 **OE □** 27 30 TCLK 29 GND **LE 1** 28

NC - No internal connection

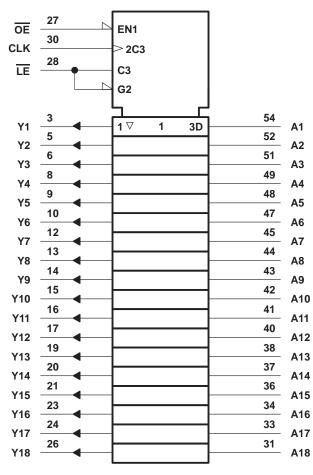


## FUNCTION TABLE (each universal bus driver)

	INP		OUTPUT	
OE	LE	CLK	Α	Υ
Н	Χ	Χ	Χ	Z
L	L	Χ	L	L
L	L	X	Н	Н
L	Н	$\uparrow$	L	L
L	Н	$\uparrow$	Н	Н
L	Н	Н	Χ	Y <sub>0</sub> † Y <sub>0</sub> ‡
L	Н	L	Χ	Y <sub>0</sub> ‡

<sup>†</sup> Output level before the indicated steady-state input conditions were established, provided that CLK is high before LE goes high

### logic symbol§

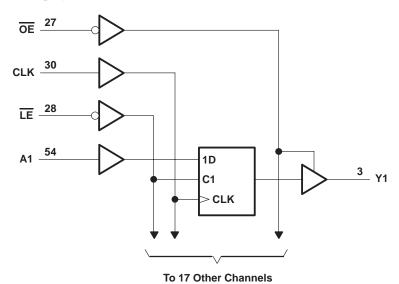


<sup>§</sup> This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.



<sup>‡</sup> Output level before the indicated steady-state input conditions were established

### logic diagram (positive logic)



### absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V <sub>CC</sub>	0.5 V to 4.6 V
Input voltage range, V <sub>I</sub> (see Note 1)	
Voltage range applied to any output in the high-impedance or power-off state, VO	
(see Note 1)	–0.5 V to 4.6 V
Voltage range applied to any output in the high or low state, VO	
(see Notes 1 and 2)	$10.5 \text{ V to V}_{CC} + 0.5 \text{ V}$
Input clamp current, I <sub>IK</sub> (V <sub>I</sub> < 0)	
Output clamp current, I <sub>OK</sub> (V <sub>O</sub> < 0)	–50 mA
Continuous output current, IO	±50 mA
Continuous current through each V <sub>CC</sub> or GND	±100 mA
Package thermal impedance, θ <sub>JA</sub> (see Note 3): DGG package	64°C/W
DGV package	48°C/W
Storage temperature range, T <sub>stq</sub>	–65°C to 150°C

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.
  - 2. The output positive-voltage rating may be exceeded up to 4.6 V maximum if the output current rating is observed.
  - 3. The package thermal impedance is calculated in accordance with JESD 51.



### recommended operating conditions (see Note 4)

			MIN	MAX	UNIT	
Voc	Supply voltage	Operating	1.4	3.6	V	
Vcc	Su <b>pp</b> iy voltage	Data retention only	1.2		l v	
		V <sub>CC</sub> = 1.2 V	VCC			
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$	0.65 × V <sub>CC</sub>			
$V_{IH}$	High-level input voltage  Low-level input voltage  Input voltage Output voltage  HS Static high-level output current†  LS Static low-level output current†	$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	0.65 × V <sub>CC</sub>		V	
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7			
		$V_{CC} = 3 V \text{ to } 3.6 V$	2	2		
		V <sub>CC</sub> = 1.2 V		GND		
		V <sub>CC</sub> = 1.4 V to 1.6 V		0.35 × V <sub>CC</sub>	V	
$V_{IL}$	Low-level input voltage	$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		$0.35 \times V_{CC}$		
		V <sub>CC</sub> = 2.3 V to 2.7 V		0.7		
		V <sub>CC</sub> = 3 V to 3.6 V		0.8	1	
٧ <sub>I</sub>	Input voltage		0	3.6	V	
V/a	Output voltage	Active state	0	Vcc	V	
٧٥	High-level input voltage  Low-level input voltage  Input voltage  Output voltage  Static high-level output current†  Input transition rise or fall rate	3-state	0	3.6	l v	
		V <sub>CC</sub> = 1.4 V to 1.6 V		-2		
1	O Output voltage	V <sub>CC</sub> = 1.65 V to 1.95 V		-4	]	
IOHS	Static nign-level output current	V <sub>CC</sub> = 2.3 V to 2.7 V		-8	mA	
		$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$		GND  0.35 × V <sub>CC</sub> 0.35 × V <sub>CC</sub> 0.7  0.8  3.6  V <sub>CC</sub> 3.6  -2  -4  -8  -12  2  4  8  12	1	
		V <sub>CC</sub> = 1.4 V to 1.6 V		2		
1	Charlie lave lavel autout average t	V <sub>CC</sub> = 1.65 V to 1.95 V		4		
lols	Static low-level output current	V <sub>CC</sub> = 2.3 V to 2.7 V		8	mA	
		V <sub>CC</sub> = 3 V to 3.6 V		12		
Δt/Δν	Input transition rise or fall rate	V <sub>CC</sub> = 1.4 V to 3.6 V		5	ns/V	
TA	Operating free-air temperature	-	-40	85	°C	

To Dynamic drive capability is equivalent to standard outputs with I<sub>OH</sub> and I<sub>OL</sub> of ±24 mA at 2.5-V V<sub>CC</sub>. See Figure 1 for V<sub>OL</sub> vs I<sub>OL</sub> and V<sub>OH</sub> vs I<sub>OH</sub> characteristics. Refer to the TI application reports, *AVC Logic Family Technology and Applications*, literature number **SCEA006**, and *Dynamic Output Control (DOC™) Circuitry Technology and Applications*, literature number **SCEA009**.

NOTE 4: All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



## electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	V <sub>CC</sub>	MIN TYPT	MAX	UNIT	
		I <sub>OHS</sub> = -100 μA	1.4 V to 3.6 V	V <sub>CC</sub> -0.2			
		$I_{OHS} = -2 \text{ mA}, \qquad V_{IH} = 0.91 \text{ V}$	1.4 V	1.05			
Voн		$I_{OHS} = -4 \text{ mA}, \qquad V_{IH} = 1.07 \text{ V}$	1.65 V	1.2		V	
		$I_{OHS} = -8 \text{ mA}, \qquad V_{IH} = 1.7 \text{ V}$	2.3 V	1.75			
		$I_{OHS} = -12 \text{ mA}, \qquad V_{IH} = 2 \text{ V}$	3 V	2.3			
		I <sub>OLS</sub> = 100 μA	1.4 V to 3.6 V		0.2		
		$I_{OLS} = 2 \text{ mA},$ $V_{IL} = 0.49 \text{ V}$	1.4 V		0.4		
VOL		$I_{OLS} = 4 \text{ mA}, \qquad V_{IL} = 0.57 \text{ V}$	1.65 V		0.45	V	
		$I_{OLS} = 8 \text{ mA}, \qquad V_{IL} = 0.7 \text{ V}$	2.3 V		0.55		
		$I_{OLS} = 12 \text{ mA}, \qquad V_{IL} = 0.8 \text{ V}$	3 V		0.7		
IĮ	Control inputs	$V_I = V_{CC}$ or GND	3.6 V		±2.5	μΑ	
I <sub>off</sub>		$V_I$ or $V_O = 3.6 V$	0		±10	μΑ	
loz		$V_O = V_{CC}$ or GND	3.6 V		±10	μΑ	
ICC		$V_I = V_{CC}$ or GND, $I_O = 0$	3.6 V		40	μΑ	
	CLK input	Vi – Voc or GND	2.5 V	4			
	CER Input	$V_I = V_{CC}$ or GND	3.3 V	4			
	Control inputs	Vi – Via a or CND	2.5 V	4		pF	
Ci	Control inputs	$V_I = V_{CC}$ or GND	3.3 V	4		рг	
	Doto inputo	Vi – Voo or CND	2.5 V	1.4 V to 3.6 V 0.2  1.4 V 0.4  1.65 V 0.45  2.3 V 0.55  3 V 0.7  3.6 V ±2.5  0 ±10  3.6 V ±10  3.6 V 40  2.5 V 4  3.3 V 4  2.5 V 4  3.3 V 4			
	Data inputs	V <sub>I</sub> = V <sub>CC</sub> or GND	3.3 V	2.5			
	Outputs	Vo - Voo er CND	2.5 V	6.5			
Co		VO = VCC or GND	3.3 V	6.5		pF	

<sup>†</sup> Typical values are measured at  $T_A = 25$ °C.

# timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 2 through 5)

		V <sub>CC</sub> = 1.2 V		V <sub>CC</sub> = 1.5 V ± 0.1 V		V <sub>CC</sub> = 1.8 V ± 0.15 V		V <sub>CC</sub> = 2.5 V ± 0.2 V		V <sub>CC</sub> = 3.3 V ± 0.3 V		UNIT						
				MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX					
fclock	Clock free	quency							150		150		150	MHz				
	Pulse	LE low						3.3		3.3		3.3						
t <sub>W</sub>	duration	duration	duration	duration	duration	CLK high or lo	ow					3.3		3.3		3.3		ns
	Setup time	Data before C	CLK <sup>↑</sup>	1		0.9		0.7		0.7		0.7						
t <sub>su</sub>			Data	CLK high	1.6		1.5		1		1		1		ns			
			before LE↑	CLK low	3.1		1.7		1.3		1		1					
		Data after CL	K↑	1.5		1.3		1		0.9		0.9						
+.	Hold time	Data after LE↑	CLK high	2.5		2		1.8		1.5		1.4		ns				
		Data after LE↑	CLK low	2		1.7		1.5		1.3		1.3						



# switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 2 through 5)

PARAMETER	FROM TO (INPUT) (OUTPUT)		V <sub>CC</sub> = 1.2 V	$V VCC = 1.5 V \pm 0.1 V$		V <sub>CC</sub> = 1.8 V ± 0.15 V		V <sub>CC</sub> = 2.5 V ± 0.2 V		V <sub>CC</sub> = 3.3 V ± 0.3 V		UNIT
	(INFO1)	(0011-01)	TYP	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f <sub>max</sub>						150		150		150		MHz
	Α		5.3	1.2	6.2	1.5	4.9	1	3.2	0.9	2.5	
t <sub>pd</sub>	LE	Y	7	2.2	9.7	1.8	7.5	1.5	4.9	0.8	4	ns
	CLK		6	1.9	7.8	1.6	6	1.1	3.7	1	3.1	
t <sub>en</sub>	ŌĒ	Υ	7.9	2.4	10.2	1.6	8.8	1.5	6.7	1	6.2	ns
t <sub>dis</sub>	OE	Y	7.7	2.1	10.3	1.5	8.4	1.2	5.3	1	5.3	ns

### switching characteristics, $T_A = 0$ °C to 85°C, $C_L = 0$ pF<sup>†</sup>

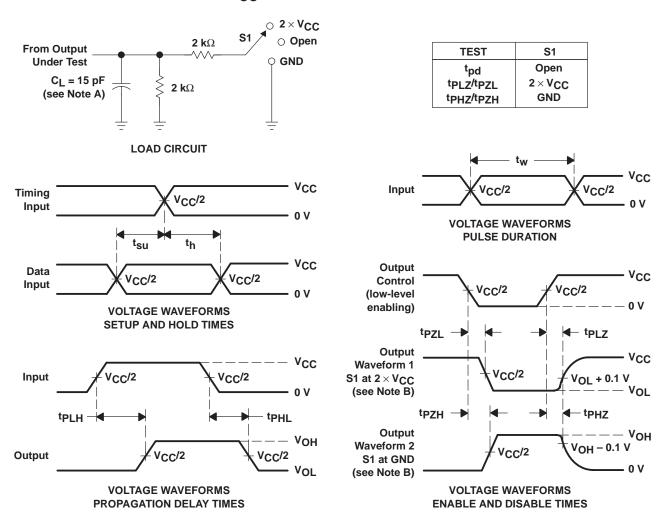
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>CC</sub> = ± 0.1	UNIT	
	(1141 01)	(6611-61)	MIN	MAX	
<sup>t</sup> pd	А	~	0.6	1.3	no
	CLK	Ť	0.7	1.5	ns

<sup>†</sup> Texas Instruments SPICE simulation data

### operating characteristics, T<sub>A</sub> = 25°C

DADAMETED			PARAMETER TEST CONDITIONS			TEST CONDITIONS VCC = 1.8 V VCC = 2.5 V VCC =		V <sub>CC</sub> = 3.3 V	UNIT	
	FARAMETER		TEST CONDITIONS	TYP	TYP	TYP	ONIT			
	Power dissipation	Outputs enabled	Cı = 0. f = 10 MHz	45	48	52	pF			
Cpd	capacitance Outputs disabled $C_L = 0$ ,		C[ = 0, 1 = 10 MH2	23	25	28	рг			

## PARAMETER MEASUREMENT INFORMATION $V_{CC}$ = 1.2 V AND 1.5 V $\pm$ 0.1 V



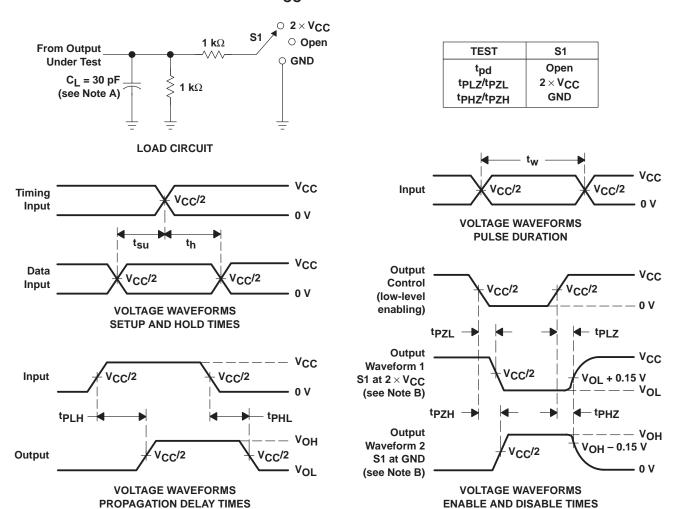
NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_Q = 50 \Omega$ ,  $t_f \leq$  2 ns,  $t_f \leq$  2 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLZ and tpHZ are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 2. Load Circuit and Voltage Waveforms



## PARAMETER MEASUREMENT INFORMATION $V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}$

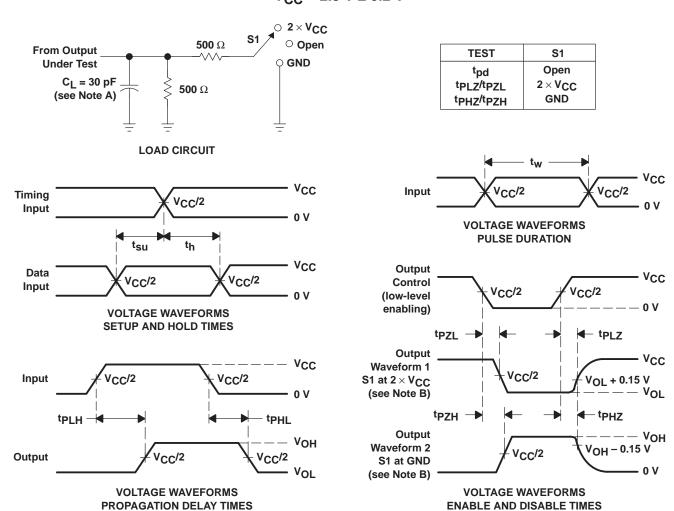


NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_O = 50 \Omega$ ,  $t_f \leq 2$  ns,  $t_f \leq 2$  ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLZ and tpHZ are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 3. Load Circuit and Voltage Waveforms

## PARAMETER MEASUREMENT INFORMATION $V_{CC}$ = 2.5 V $\pm$ 0.2 V

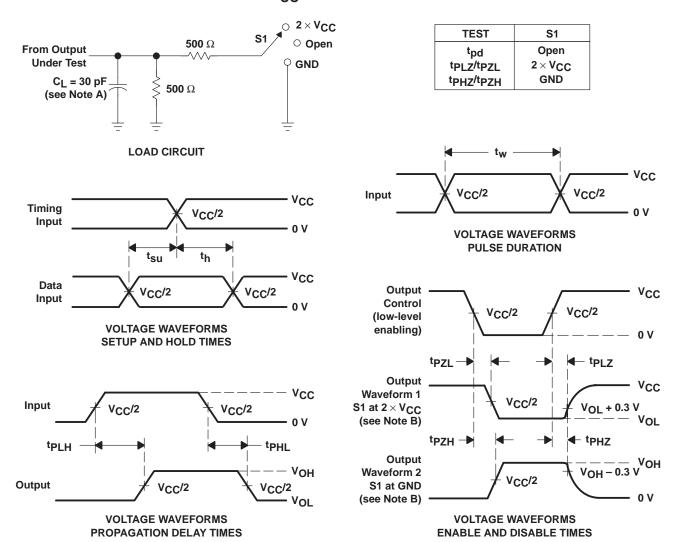


- NOTES: A. C<sub>L</sub> includes probe and jig capacitance.
  - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
  - C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_Q = 50~\Omega$ ,  $t_f \leq$  2 ns,  $t_f \leq$  2 ns.
  - D. The outputs are measured one at a time with one transition per measurement.
  - E. tpLz and tpHz are the same as tdis.
  - F. tpzL and tpzH are the same as ten.
  - G. tpLH and tpHL are the same as tpd.

Figure 4. Load Circuit and Voltage Waveforms



## PARAMETER MEASUREMENT INFORMATION $V_{CC}$ = 3.3 V $\pm$ 0.3 V



NOTES: A. C<sub>I</sub> includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_O = 50 \Omega$ ,  $t_f \leq 2$  ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpl 7 and tpH7 are the same as tdis.
- F. t<sub>PZL</sub> and t<sub>PZH</sub> are the same as t<sub>en</sub>.
- G. tpLH and tpHL are the same as tpd.

Figure 5. Load Circuit and Voltage Waveforms



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